

**JSCJ TO-251-3L Plastic-Encapsulate Transistors****3DA752** TRA NSISTOR (NPN)**FEATURES**

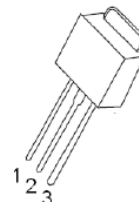
- Power Dissipation

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	2	A
P_C	Collector power dissipation	1.2	W
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55-150	$^{\circ}\text{C}$

TO-251-3L

- 1.BASE
2.COLLECTOR
3.EMITTER

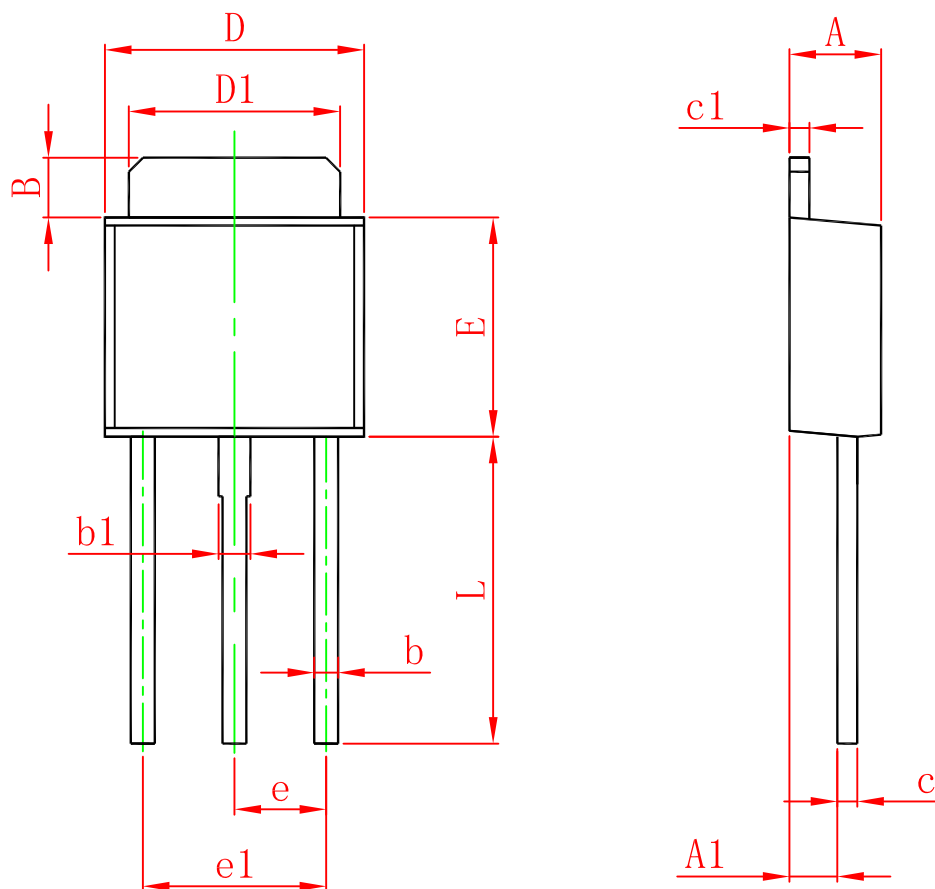
**ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\text{mA}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=2\text{V}, I_C=500\text{mA}$	100		400	
Collector-emitter saturation voltage	$V_{CE(sat)1}$	$I_C=2\text{A}, I_B=0.2\text{A}$			0.8	V
	$V_{CE(sat)2}$	$I_C=1.5\text{A}, I_B=30\text{mA}$			2	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=500\text{mA}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		13		pF

CLASSIFICATION OF h_{FE}

Rank	O	Y	G
Range	100-200	160-320	200-400

TO-251-3L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.050	1.350	0.042	0.054
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	7.500	7.900	0.295	0.311